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**AMENDMENTS TO THE CLAIMS:**

**Please cancel claims 8-14 and 20-22 without prejudice or disclaimer.**

1. (Previously presented) A group III nitride compound semiconductor light-emitting device, comprising:
  - a semiconductor laminate portion including a light-emitting layer; and
  - a reflection surface disposed so as to be opposite to a side surface of said light-emitting layer,  
wherein said semiconductor laminate portion and said reflection surface are provided on the same chip, and a predetermined distance is provided between said semiconductor laminate portion and said reflection surface.
2. (Previously presented) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein said reflection surface reflects light emitted from said side surface of said semiconductor laminate portion into a direction of an optical axis of said light-emitting device.
3. (Previously presented) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein said predetermined distance comprises a distance between said reflection surface and said side surface of said semiconductor laminate portion which is in a range of from 0.1 to 10 $\mu$ m.
4. (Previously presented) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein said reflection surface comprises a material which is the same as that of an n pad electrode.
5. (Original) A group III nitride compound semiconductor light-emitting device according to claim 4, wherein a portion of said n pad electrode opposite to said side surface of said semiconductor laminate portion forms a second reflection surface.
6. (Previously presented) A group III nitride compound semiconductor light-emitting

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device according to claim 4, wherein said reflection surface is formed on an n-type semiconductor layer which is formed by etching to a first depth, and said n pad electrode is formed on said n-type semiconductor layer which is formed by etching to a second depth shallower than said first depth.

7. (Original) A group II nitride compound semiconductor light-emitting device according to claim 4, wherein said reflection surface is formed integrally with said n pad electrode.

8-14. (Canceled)

15. (Previously presented) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein said predetermined distance comprises a distance between said reflection surface and said side surface of said semiconductor laminate portion which is in a range of 0.2  $\mu\text{m}$  to 7  $\mu\text{m}$ .

16. (Previously presented) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein said predetermined distance comprises a distance between said reflection surface and said side surface of said semiconductor laminate portion which is in a range of 0.3  $\mu\text{m}$  to 5  $\mu\text{m}$ .

17. (Previously presented) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein said reflection surface is formed on a layer in said semiconductor laminate portion.

18. (Previously presented) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein an upper surface of said reflection surface is elevated higher than said light-emitting layer.

19. (Previously presented) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein said reflection surface comprises a curved reflection

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surface.

20-22. (Canceled)

23. (New) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein said reflection surface reflects light emitted from said side surface of said semiconductor laminate portion

24. (New) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein said reflection surface comprises a shape for reflecting light in a direction of an optical axis for said light-emitting device.

25. (New) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein said predetermined distance comprises a distance between said reflection surface and said side surface of said semiconductor laminate portion which is no greater than 10 $\mu$ m.

26. (New) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein said direction of an optical axis comprises a direction of a center axis of said device.

27. (New) A group III nitride compound semiconductor light-emitting device according to claim 1, further comprising:

an n-pad electrode formed on said semiconductor laminate portion, said reflection surface comprising a side surface of said n-pad electrode having a shape for reflecting light in a direction of an optical axis for said light-emitting device.

28. (New) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein said reflection surface is formed around a circumference of said light-emitting layer.

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29. (New) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein at least a portion of said reflection surface is formed near a plane of said light-emitting layer.
30. (New) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein said reflection surface is disposed so as to be transversely opposite to a side surface of said light-emitting layer.
31. (New) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein said reflection surface comprises a thickness of at least 0.7 $\mu$ m.
32. (New) A group III nitride compound semiconductor light-emitting device, comprising:  
a semiconductor laminate portion including a light-emitting layer; and  
a reflection surface formed on a same chip as said semiconductor laminate portion,  
and opposing a side surface of said light-emitting,  
wherein a predetermined distance is provided between said semiconductor laminate portion and said reflection surface.